

**ADVANCED  
POWER  
TECHNOLOGY®**

**APT20M45BNR 200V 58A 0.045Ω**

**APT20M60BNR 200V 50A 0.060Ω**

## POWER MOS IV®

**UIS RATED**

### N-CHANNEL ENHANCEMENT MODE LOW VOLTAGE POWER MOSFETS

#### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT20M45BNR	APT20M60BNR	UNIT
$V_{DSS}$	Drain-Source Voltage	200	200	Volts
$I_D$	Continuous Drain Current @ $T_C = 25^\circ\text{C}$	58	50	Amps
$I_{DM}$	Pulsed Drain Current ①	238	200	
$V_{GS}$	Gate-Source Voltage Continuous	±20		Volts
$V_{GSM}$	Gate-Source Voltage Transient	±30		
$P_D$	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	360		Watts
	Linear Derating Factor	2.9		W/°C
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150		°C
$T_L$	Lead Temperature: 0.063" from Case for 10 Sec.	300		
$I_{AR}$	Avalanche Current ① (Repetitive and Non-Repetitive)	58		Amps
$E_{AR}$	Repetitive Avalanche Energy ②	30		mJ
$E_{AS}$	Single Pulse Avalanche Energy ④	1300		

#### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$BV_{DSS}$	Drain-Source Breakdown Voltage ( $V_{GS} = 0\text{V}$ , $I_D = 1.0\text{mA}$ )	200			Volts
$I_D(\text{ON})$	On State Drain Current ② ( $V_{DS} > I_D(\text{ON}) \times R_{DS}(\text{ON})$ Max, $V_{GS} = 10\text{V}$ )	APT20M45BNR	58		Amps
		APT20M60BNR	50		
$R_{DS}(\text{ON})$	Drain-Source On-State Resistance ② ( $V_{GS} = 10\text{V}$ , $0.5 I_D$ [Cont.])	APT20M45BNR		0.045	Ohms
		APT20M60BNR		0.060	
$I_{DSS}$	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}$ , $V_{GS} = 0\text{V}$ )			250	$\mu\text{A}$
	Zero Gate Voltage Drain Current ( $V_{DS} = 0.8 V_{DSS}$ , $V_{GS} = 0\text{V}$ , $T_C = 125^\circ\text{C}$ )			1000	
$I_{GSS}$	Gate-Source Leakage Current ( $V_{GS} = \pm 20\text{V}$ , $V_{DS} = 0\text{V}$ )			±100	nA
$V_{GS(\text{TH})}$	Gate Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 1.0\text{mA}$ )	2	4		Volts

#### THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.34	$^\circ\text{C}/\text{W}$
$R_{\theta JA}$	Junction to Ambient			40	

CAUTION: These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

405 S.W. COLUMBIA STREET  
BEND, OREGON 97702-1035  
U.S.A.

PHONE . . . (503) 382-8028

FAX . . . . . (503) 388-0364

## DYNAMIC CHARACTERISTICS

APT20M45/20M60BNR

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		5510	6500	pF
$C_{oss}$	Output Capacitance			1090	1400	
$C_{rss}$	Reverse Transfer Capacitance			290	450	
$Q_g$	Total Gate Charge ③	$V_{GS} = 10V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D[\text{Cont.}] @ 25^\circ C$		165	220	nC
$Q_{gs}$	Gate-Source Charge			43	70	
$Q_{gd}$	Gate-Drain ("Miller") Charge			80	110	
$t_d(\text{on})$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 0.5 V_{DSS}$ $I_D = I_D[\text{Cont.}] @ 25^\circ C$		20	30	ns
$t_r$	Rise Time			60	90	
$t_d(\text{off})$	Turn-off Delay Time			110	140	
$t_f$	Fall Time	$R_G = 1.8\Omega$		60	90	

## SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions		MIN	TYP	MAX	UNIT
$I_S$	Continuous Source Current (Body Diode)	APT20M45BNR			58	Amps
		APT20M60BNR			50	
$I_{SM}$	Pulsed Source Current ① (Body Diode)	APT20M45BNR			232	
		APT20M60BNR			200	
$V_{SD}$	Diode Forward Voltage ② ( $V_{GS} = 0V$ , $I_S = -I_D$ [Cont.])				1.5	Volts
$t_{rr}$	Reverse Recovery Time ( $I_S = -I_D$ [Cont.], $dI_S/dt = 100A/\mu s$ )			400		ns
$Q_{rr}$	Reverse Recovery Charge ( $I_S = -I_D$ [Cont.], $dI_S/dt = 100A/\mu s$ )			N/A		$\mu C$

## **SAFE OPERATING AREA CHARACTERISTICS**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
SOA1	Safe Operating Area	$V_{DS} = 0.4 V_{DSS}$ , $I_{DS} = P_D / 0.4 V_{DSS}$ , $t = 1 \text{ Sec.}$	360			Watts
SOA2	Safe Operating Area	$I_{DS} = I_D$ [Cont.], $V_{DS} = P_D / I_D$ [Cont.], $t = 1 \text{ Sec.}$	360			
$I_{LM}$	Inductive Current Clamped		APT20M45BNR	232		Amps
			APT20M60BNR	200		

① Repetitive Rating: Pulse width limited by maximum junction temperature

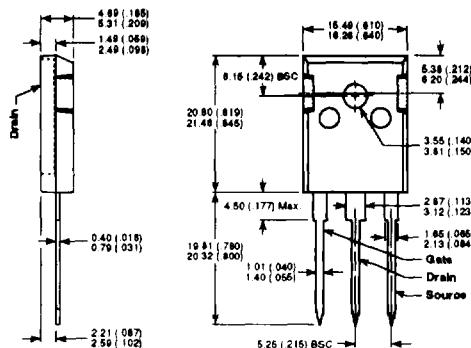
<sup>③</sup> See MIL-STD-750 Method 3471.

④ Starting  $T_1 = 25^\circ\text{C}$ ,  $L = 773\mu\text{H}$ ,  $R_G = 25\Omega$ , Peak  $I_1 = 58\text{A}$

② Pulse Test: Pulse width < 380 μS, Duty Cycle < 2%

**APT Reserves the right to change, without notice, the specifications and information contained herein.**

## **TO-247AD Package Outline**



Dimensions in Millimeters and Inches